

Title (en)

METHOD FOR THE PRODUCTION OF A COMPOSITE SICOI-TYPE SUBSTRATE COMPRISING AN EPITAXY STAGE

Title (de)

HERSTELLUNGSVERFAHREN EINES SICOI-SUBSTRATS MIT EINEM EPITAXIESCHRITT

Title (fr)

PROCEDE DE FABRICATION D' UN SUBSTRAT COMPOSITE DU TYPE SICOI COMPRENANT UNE ETAPE D' EPITAXIE

Publication

EP 1547145 A2 20050629 (FR)

Application

EP 03780258 A 20030901

Priority

- FR 0350044 W 20030901
- FR 0210884 A 20020903

Abstract (en)

[origin: FR2844095A1] Fabrication of a composite SiCOI substrate comprises the provision of an initial substrate incorporating a support (1) of Si or SiC supporting a layer (2) of SiO₂ carrying a thin film (3) of SiC and the epitaxy of SiC (4) on the thin film of SiC. The epitaxy is realised at the following temperatures: (a) from 1450 degrees C to obtain an epitaxy of polytype 6H or 4H on a carried thin film of polytype 6H or 4H respectively, if the support is of SiC; (b) from 1350 degrees C to obtain an epitaxy of polytype 3C on a carried thin layer of polytype 3C, if the support is of Si or SiC; (c) from 1350 degrees C to obtain an epitaxy of polytype 6H or 4H on a carried thin film of polytype 6H or 4H respectively, if the support is of Si. An Independent claim is also included for a semiconductor device produced on a composite SiCOI substrate obtained.

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H01L 21/76

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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